

Basics of Active and Nonlinear HF Electronics – Tutorial

We consider a FET and its nonlinear drain current source I_{DS} modeled by the below equation as a function of its control voltages V_{GS} and V_{DS} :

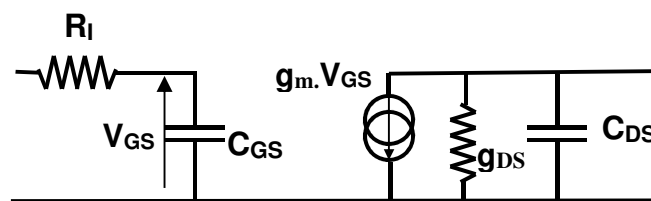
$$I_{DS} = I_{DSS} \left[1 - \frac{V_{GS}(t)}{V_P} \right]^2 (1 + K \cdot V_{DS}(t))$$

The model is accurate in the variation range $-1.5V < V_{GS} < 0V$; $1V < V_{DS} < 7V$

with $I_{DSS} = 60 \text{ mA}$; $V_P = -1.5 \text{ V}$; $K = 0.05$; $C_{GS} = 0.5 \text{ pF}$; $C_{DS} = 0.1 \text{ pF}$; $R_I = 4 \Omega$.

The FET is biased at $V_{GS0} = -0.75 \text{ V}$ and $V_{DS0} = 4 \text{ V}$

The small signal linear model of the FET in these conditions is shown below:



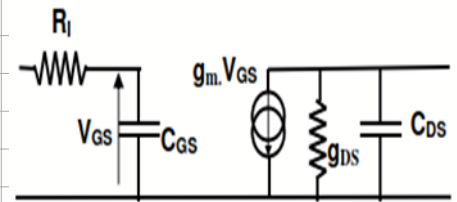
Study of parallel-cells of FET

- 1) Draw the I_{DS} - V_{DS} curves in the variation range
- 2) Determine the values of transconductance g_m and drain conductance g_{DS} at the selected bias point.
- 3) Determine the ^{scaling rules} small-signal linear model corresponding to n parallel-cells of the FET. Determine the variation laws that give equivalent elements ($C_{GS}(n)$...) of the parallel-cells as a function of the number of cells n and the equivalent elements ($C_{GS}(1)$...) of a single-cell FET.
- 4) { Determine the maximum power gain G_{MAX} for an ideal power matching at small-signal (linear) level. Determine its cutoff frequency f_c and its maximum frequency f_{MAX} .
- 5) After determining the optimum power load in large signal class A operation, determine the maximum gain G_{MAX} in this loading condition. Estimate the maximum output power value in class A. Compare these values to G_{MAX} and its associated maximum output power when the FET is ideally matched to give optimum gain in small signal operation.
- 6) Same questions 4) and 5) in the case of n -parallel FETs

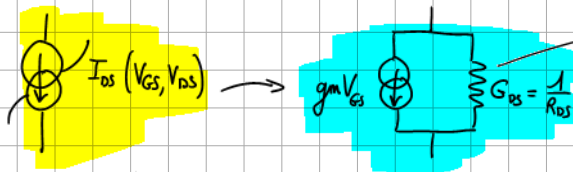
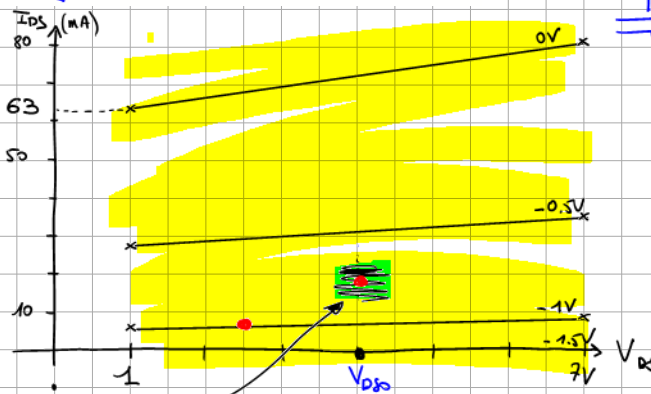
$$I_{DS} = I_{DSS} \left[1 - \frac{V_{GS}(t)}{V_P} \right]^2 (1 + K \cdot V_{DS}(t)) \quad *$$

The model is accurate in the variation range $-1.5V < V_{GS} < 0V$; $1V < V_{DS} < 7V$
 with $I_{DSS} = 60 \text{ mA}$; $V_P = -1.5 \text{ V}$; $K = 0.05$; $C_{GS} = 0.5 \text{ pF}$; $C_{DS} = 0.1 \text{ pF}$; $R_i = 4 \Omega$.

The FET is biased at $V_{GS0} = -0.75 \text{ V}$ and $V_{DS0} = 4 \text{ V}$ Bias point



V_{GS}	V_{DS}	$\left(1 - \frac{V_{GS}}{V_P}\right)^2$	$1 + K V_{DS}$	I_{DS}
0V	1V	1	1.05	63 mA
	7V		1.35	81 mA
-0.5V	1V	$\left(1 - \frac{-0.5}{-1.5}\right)^2 = \frac{4}{9}$	1.05	28 mA
	7V		1.35	36 mA
-1V	1V	$\left(1 - \frac{-1}{-1.5}\right)^2 = \frac{1}{9}$	1.05	7 mA
	7V		1.35	9 mA



$$f(x, y) = f(x_0, y_0) + df$$

$$\begin{cases} x = x_0 + dx \\ y = y_0 + dy \end{cases}$$

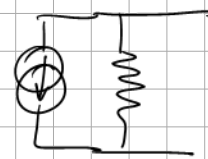
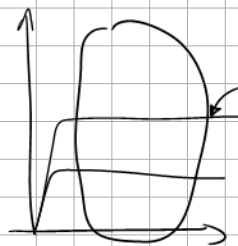
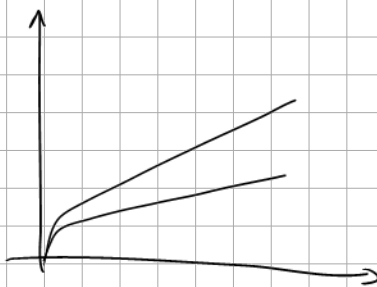
$$df = \left(\frac{\partial f}{\partial x} \right)_{(x_0, y_0)} dx + \left(\frac{\partial f}{\partial y} \right)_{(x_0, y_0)} dy$$

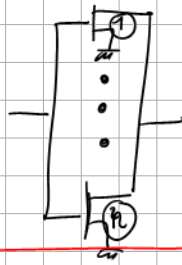
$$I_{DS} = I_{DSS} \left[1 - \frac{V_{GS}(t)}{V_P} \right]^2 (1 + K \cdot V_{DS}(t))$$

$$g_m(V_{GS}, V_{DS}) = \left(\frac{\partial I_{DS}}{\partial V_{GS}} \right)_{(V_{GS0}, V_{DS0})} = -2 \frac{I_{DSS}}{V_P} \left(1 - \frac{V_{GS0}}{V_P} \right) (1 + K V_{DS0}) = -2 \frac{60 \text{ mA}}{-1.5} \left(1 - \frac{-0.75}{-1.5} \right) (1 + 0.05 \times 4) = 48 \text{ m}\Omega^{-1}$$

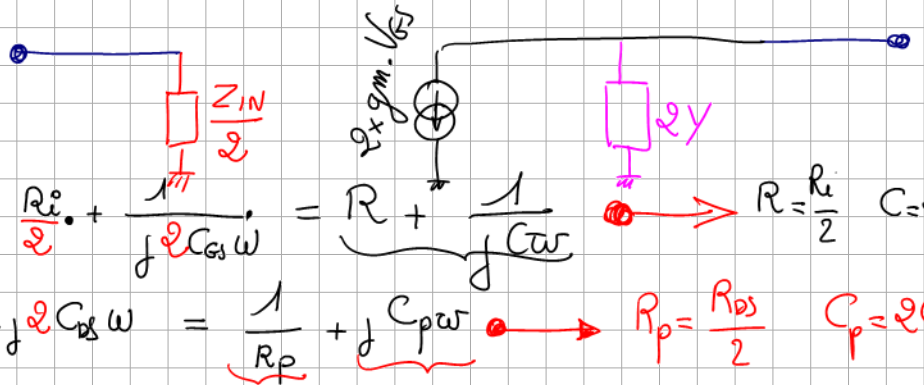
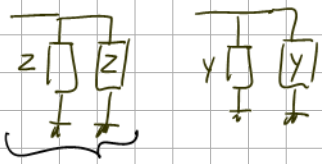
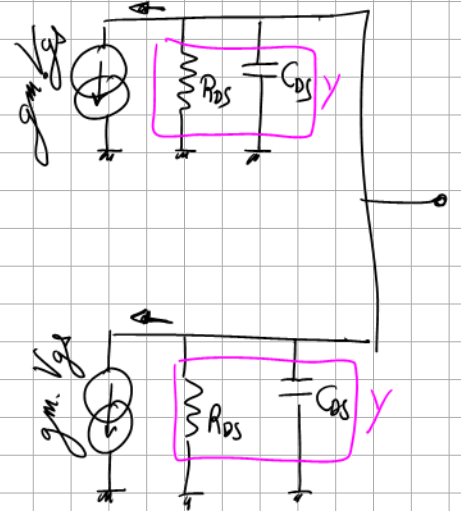
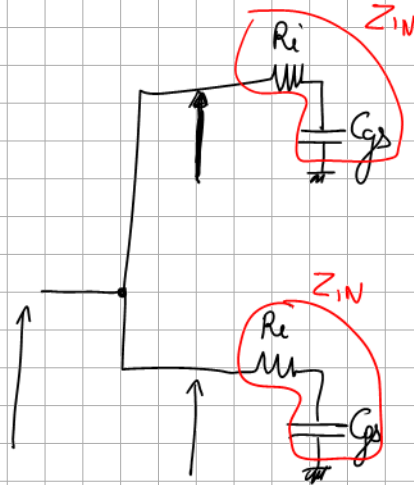
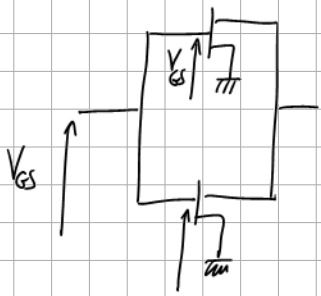
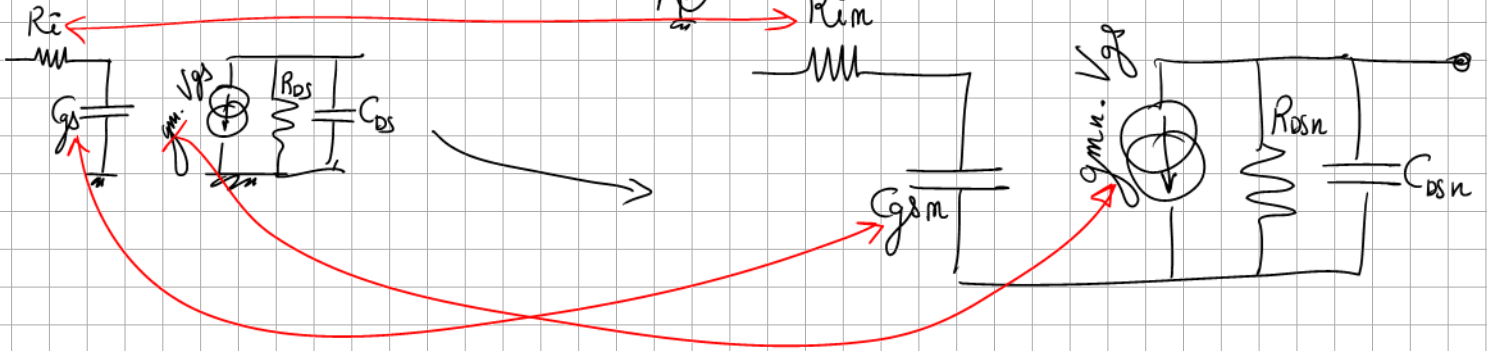
$$g_{DS} = \left(\frac{\partial I_{DS}}{\partial V_{DS}} \right)_{(V_{GS0}, V_{DS0})} = K I_{DSS} \left(1 - \frac{V_{GS0}}{V_P} \right)^2 = 0.005 \times 60 \text{ mA} \left(1 - \frac{-0.75}{-1.5} \right)^2 = 0.75 \text{ m}\Omega^{-1}$$

$$R_{DS} = \frac{1}{g_{DS}} = 1.3 \text{ k}\Omega$$



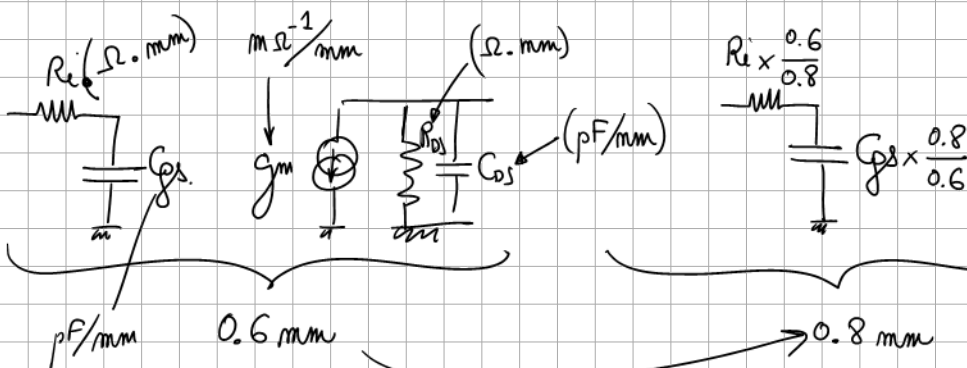


scaling rules



$$Z_{IN} = R_i + \frac{1}{j\omega C_{gs}} \rightarrow \frac{Z_{IN}}{2} = \frac{R_i}{2} + \frac{1}{j\omega 2C_{gs}} = R + \frac{1}{j\omega C}$$

$$Y = \frac{1}{R_{ds}} + j\omega C_{ds} \rightarrow 2Y = \frac{2}{R_{ds}} + j\omega 2C_{ds} = \frac{1}{R_p} + j\omega C_p \rightarrow R_p = \frac{R_{ds}}{2} \quad C_p = 2C_{ds}$$

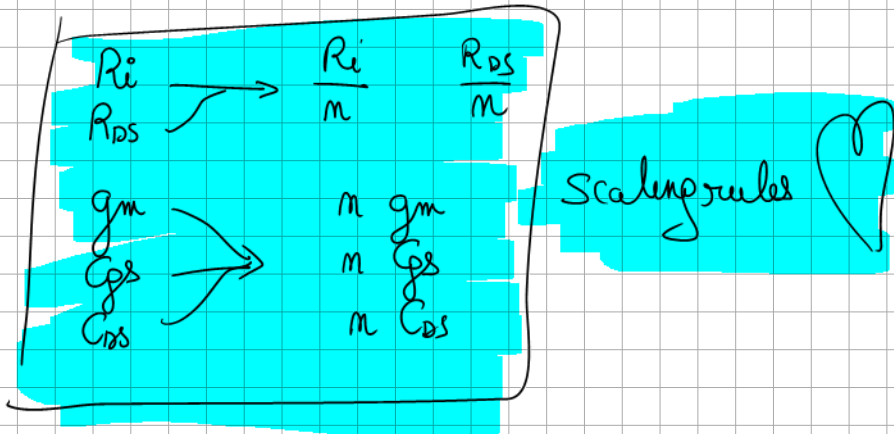


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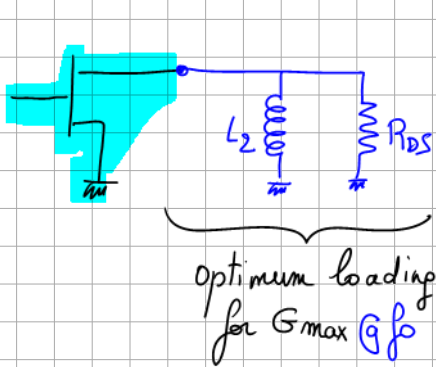
Technology :

$$\left. \begin{aligned} R_i &= 1 \Omega \cdot \text{mm} \times \\ R_{DS} &= 125 \Omega \cdot \text{mm} \times \\ C_{gs} &= 2 \text{ pF} / \text{mm} \times \end{aligned} \right\}$$

$$\begin{aligned} T_1 &\rightarrow 8 \times 75 \mu\text{m} = 0.6 \text{ mm} \\ R_{e1} &= \frac{1 \Omega \cdot \text{mm}}{0.6} \\ R_{DS1} &= \frac{125}{0.6} \\ C_{gs1} &= 2 \text{ pF} \times 0.6 \end{aligned}$$



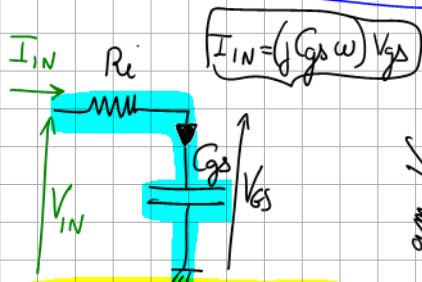
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$$Y_{CDS} = j C_{DS} \omega_0 \quad \oplus \quad Y_{L2} = \frac{-j}{L_2 \omega_0} = 0$$

$$C_{DS} \omega_0 = \frac{1}{L_2 \omega_0}$$

$$L_2 = \frac{1}{C_{DS} \omega_0^2}$$



$$I_{IN} = (j C_{gs} \omega) V_{gs}$$

$$P_{IN} = \frac{1}{2} \text{Re}(V_{IN} I_{IN}^*) = \frac{1}{2} \text{Re} \left(\left[R_i + \frac{1}{j C_{gs} \omega} \right] I_{IN} \times I_{IN}^* \right) = \frac{1}{2} R_i |I_{IN}|^2 = \frac{1}{2} R_i |j C_{gs} \omega V_{gs}|^2$$

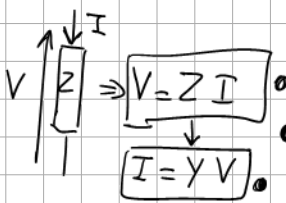
$$= \frac{1}{2} R_i C_{gs}^2 \omega^2 |V_{gs}|^2$$

$$P_{OUT} = \frac{1}{2} \text{Re}(V_{OUT} I_{OUT}^*) = \frac{1}{2} \text{Re} \left(V_{OUT} \frac{V_{OUT}^*}{R_{DS}} \right) = \frac{1}{2} \frac{|V_{OUT}|^2}{R_{DS}} = \frac{1}{2} \frac{g_m^2 R_{DS}^2}{4 R_{DS}} |V_{gs}|^2$$

$$= \frac{1}{8} g_m^2 R_{DS} |V_{gs}|^2$$

$$G_{max} = \frac{P_{OUT}}{P_{IN}} = \frac{g_m^2 R_{DS}}{4 R_i C_{gs}^2 \omega^2}$$

$$V_{OUT} = - \frac{g_m R_{DS}}{2} V_{gs}$$



POWER

MATCHING

